2SB1050

Silicon PNP epitaxial planar type

For low-frequency amplification

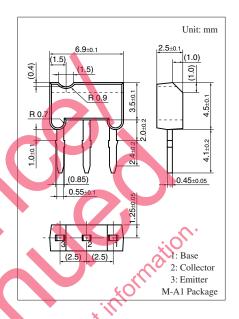
■ Features

- Low collector-emitter saturation voltage V_{CE(sat)}
- Large collctor current I_C
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-30	V	
Collector-emitter voltage (Base open)	V _{CEO}	-20	V	
Emitter-base voltage (Collector open)	V_{EBO}	-7	V	
Collector current	I_C	-5	A	
Peak collector current	I_{CP}	-8	A	
Collector power dissipation *	P _C	1	W	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Note) *: Print circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion



■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

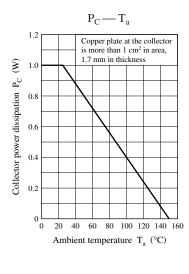
Collector power dissipation *	C	1 W	•	KO		l Package			
Junction temperature T _i 150 °C									
Junction temperature T _j 150 Storage temperature T _{stg} −55 to +150 °C Note) *: Print circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion ■ Electrical Characteristics T _a = 25°C ± 3°C									
Note) *: Print circuit board: Copper foil area of 1 cm ² or more, and the board									
thickness of 1.7 mm for the collector portion									
apo agui									
■ Electrical Characteristics T _a =	25°C ±	-3°C							
Parameter Sy	ymbol	Conditions	Min	Тур	Max	Unit			
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-20			V			
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mathrm{pA}, I_C = 0$				V			
Collector-base cutoff current (Emitter open)	I _{CBO}				-100	nA			
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -5 V_{*} I_{C} = 0$			-100	nA			
Forward current transfer ratio *1, 2	h _{FE}	$V_{CE} = -2 \text{ V}, I_{C} = -2 \text{ A}$	90		625	_			
Collector-emitter saturation voltage *1 V	E(sat)	$I_C = -3 \text{ A}, I_B = -0.1 \text{ A}$			-1	V			
Transition frequency	f_T	$V_{CB} = -6 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz			
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			85	pF			

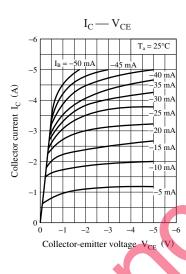
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

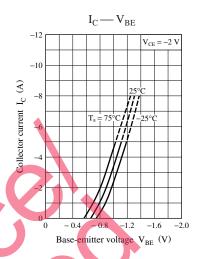
2. *1: Pulse measurement

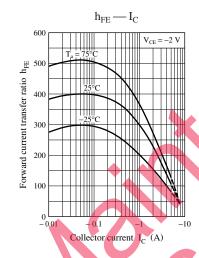
*2: Rank classification

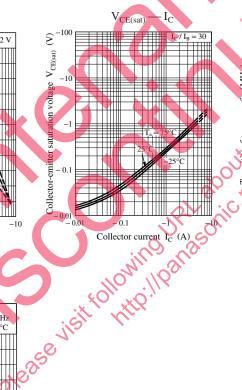
Rank	Р	Q	R
h _{FE}	90 to135	120 to 205	180 to 625

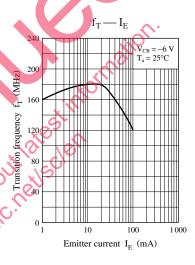


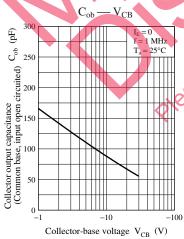












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